



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

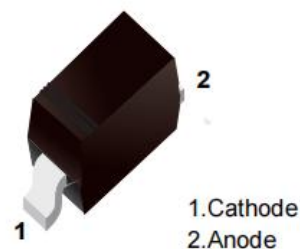
1N4001WS-6AF~1N4007WS-6AF

SOD-323 General Purpose Rectifier Diode 通用整流二极管



■Features 特点

Low forward voltage drop 低正向压降
Low reverse leakage current 低反向漏电流
High surge current capability 高浪涌电流能力
High Reliability 高可靠性
Case 封装:SOD-323



■Maximum Rating 最大额定值

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	1N400 1WS -6AF	1N400 2WS -6AF	1N400 3WS -6AF	1N400 4WS -6AF	1N400 5WS -6AF	1N400 6WS -6AF	1N400 7WS -6AF	Unit 单位
Marking 印字		1A	2A	3A	4A	5A	6A	7A	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	50	100	200	400	600	800	1000	V
DC Reverse Voltage 直流反向电压	V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	35	70	140	280	420	560	700	V
Forward Rectified Current 正向整流电流	I _F	1							A
Peak Surge Current 峰值浪涌电流	I _{FSM}	25							A
Thermal Resistance Junction-Lead 结到管脚热阻	R _{θJL}	35							°C/W
Junction and Storage Temperature 结温和储藏温度	T _J , T _{stg}	150°C, -55to+150°C							

■Electrical Characteristics 电特性

(T_A=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位	Test Condition 测试条件
Forward Voltage 正向电压	V _F		0.92 0.98	1.1	V	I _F =0.5A I _F =1A
Reverse Current(T _A =25°C /) 反向电流(T _A =125°C /)	I _R			5 50	uA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _D		15		pF	V _R =4V, f=1MHz

■ Typical Characteristic Curve 典型特性曲线

Fig.1 Forward Current Derating Curve

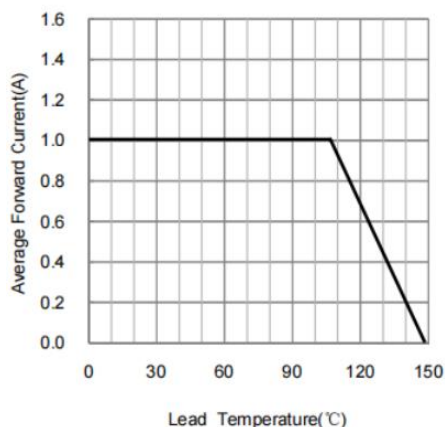


Fig.2 Maximum Non-Repetitive Peak Forward Surge Current

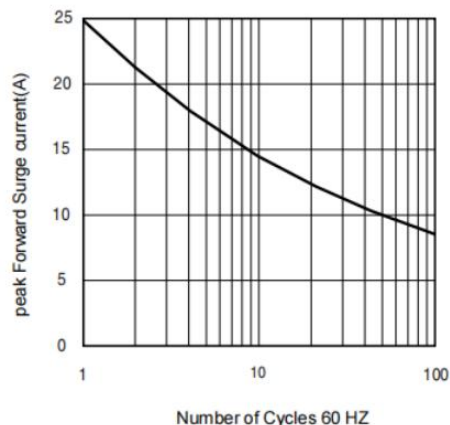


Fig.3 Typical Instantaneous Forward Characteristics

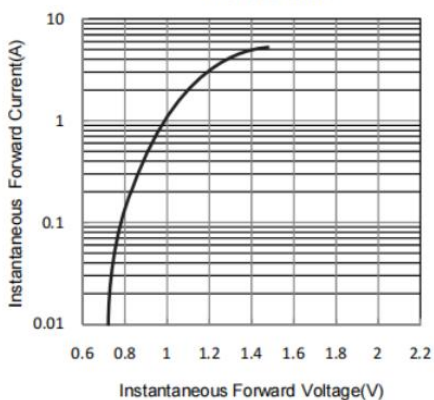
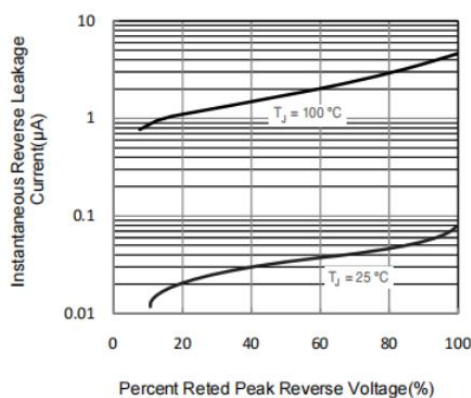
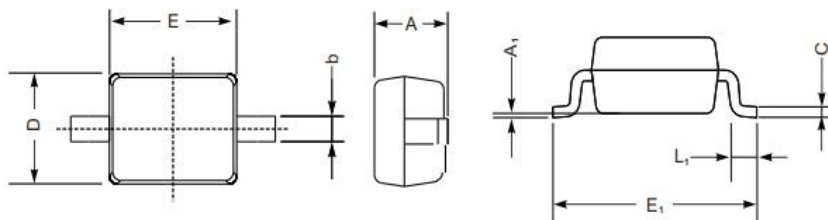


Fig.4 Typical Reverse Leakage Characteristics



■ Dimension 外形封装尺寸



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—
mil	max	43	5.9	55	70	108	16	16	8
	min	32	3.1	47	63	100	9.8	7.9	—